Cost-Effective High-Performance Monolithic X-Band Low-Noise Amplifiers (Dec. 1986 [T-MTT])

D.C. Wang, R.G. Pauley, S.-K. Wang and L.C.T. Liu. "Cost-Effective High-Performance Monolithic X-Band Low-Noise Amplifiers (Dec. 1986 [T-MTT])." 1986 Transactions on Microwave Theory and Techniques 34.12 (Dec. 1986 [T-MTT] (1986 Symposium Issue)): 1553-1558.

A low-cost, high-performance X-band amplifier with ion-implanted MESFET technology has been demonstrated. Various design, material, and processing approaches have been evaluated in terms of yield, cost, and device performance. An average noise figure of 2.2 dB and a standard deviation of 0.1 dB, with an associated gain of 22.5 dB and a standard deviation of 0.8 dB at the center frequency band of 9.5 GHz, have been measured.

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